

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	(dry adj etching) and gate and sidewall and polysilicon and polymer and polymerization and CD	USPAT	OR	ON	2004/12/08 17:19
L2	4	(first adj dry adj etching) and (second adj dry etching) and (third adj dry adj etching) and polymer and polysilicon and gate	USPAT	OR	ON	2004/12/08 17:25
L3	4	2 and (etching or process or dry or condition or polysilicon or polymers or CD or critical or demension or polymerization or potion or lower or upper or photo or mask or gate or electrode or side or wall or plasma or mT or sccm)	USPAT	OR	ON	2004/12/08 17:39
L4	1	"5491100".PN.	USPAT; USOCR	OR	ON	2004/12/08 17:36
L5	1	"5431770".PN.	USPAT; USOCR	OR	ON	2004/12/08 17:38
L6	1	"5416037".PN.	USPAT; USOCR	OR	ON	2004/12/08 17:38
L7	1	"5160408".PN.	USPAT; USOCR	OR	ON	2004/12/08 17:38
L8	1	7 and (etching or process or dry or condition or polysilicon or polymers or CD or critical or demension or polymerization or potion or lower or upper or photo or mask or gate or electrode or side or wall or plasma or mT or sccm)	USPAT	OR	ON	2004/12/08 17:50
L9	1	("5880035").PN.	USPAT	OR	OFF	2004/12/08 17:41
L10	1	9 and (etching or process or dry or condition or polysilicon or polymers or CD or critical or demension or polymerization or potion or lower or upper or photo or mask or gate or electrode or side or wall or plasma or mT or sccm)	USPAT	OR	ON	2004/12/08 17:41
L11	1782	438/706	USPAT	OR	ON	2004/12/08 17:50
L12	221	438/709	USPAT	OR	ON	2004/12/08 17:51
L13	1122	438/725	USPAT	OR	ON	2004/12/08 17:51
L14	760	438/734	USPAT	OR	ON	2004/12/08 17:51
L15	1022	438/738	USPAT	OR	ON	2004/12/08 17:51